21. (Twice amended) An electro-optical device of an active matrix comprising:

a first pixel electrode formed on a first gate line with an insulator therebetween wherein said first gate line is provided on a substrate;

a second pixel electrode formed on a second gate line with said insulator therebetween, said second pixel electrode being formed adjacent to said first pixel electrode, wherein said second gate line is provided on said substrate;

a date line provided on said substrate;

an exclusive wiring provided on said substrate, said exclusive wiring being formed between said first and second gate lines and being formed under said first pixel electrode with said insulator therebetween;

[a pixel electrode provided on said substrate and superposed on said gate line with an insulator therebetween and superposed on said wiring with an insulator therebetween;] and

at least one transistor provided on said substrate and connected with said first gate line at a gate thereof and connected with said data line at one of source and drain thereof and connected with said first pixel electrode at the other one of the source and drain wherein a first capacitance between said first pixel electrode and said first gate line and a second capacitance between said first pixel electrode and said exclusive wiring are the same as each other.

25. (Amended) An electro-optical device of an active matrix comprising:

a gate line provided on a substrate;

a date line provided on said substrate;

a wiring provided on said substrate;

a pixel electrode provided on said substrate and superposed on said gate line with an insulator therebetween to form a first capacitance and superposed on said wiring with an insulator therebetween to form a second capacitance; [and]

a first means for applying a first signal to said gate line;